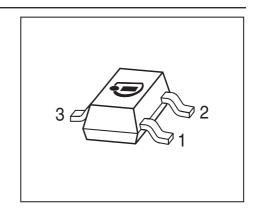


NPN Bipolar RF Transistor

- For broadband amplifiers up to 2 GHz and fast non-saturated switches at collector currents from 0.5 mA to 20 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR92P	GFs	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$	15	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2.5	
Collector current	I _C	45	mA
Base current	l _B	4	
Total power dissipation ¹⁾	P _{tot}	280	mW
<i>T</i> _S ≤ 88 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T_{Stq}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	220	K/W

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¹T_S is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	•				
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I _{CES}	-	-	10	μA
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	100	μA
$V_{\rm EB} = 2.5 \rm V, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					



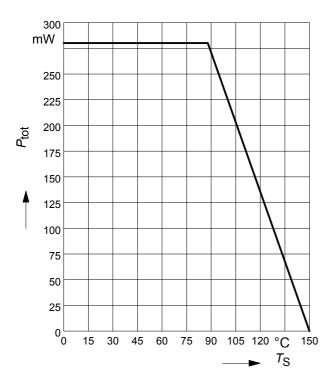
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random samplin	g)				
Transition frequency	f_{T}	3.5	5	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.39	0.55	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.23	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.64	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	1.4	-	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 1.8 GHz		-	2	-	
Power gain, maximum available ¹⁾	G _{ma}				1
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz		-	16	-	
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz		-	10.5	-	
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		_	13	_	
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 MHz		_	7.5	_	

 $^{^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$

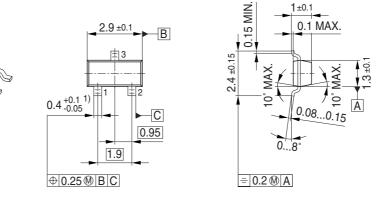


Total power dissipation $P_{tot} = f(T_S)$



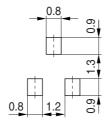


Package Outline

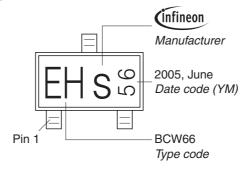


1) Lead width can be 0.6 max. in dambar area

Foot Print

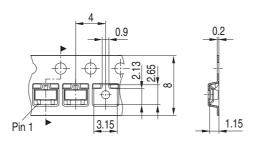


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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